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- Each Device Drives 32 Lines
- 60-V Output Voltage Swing Capability
- 25-mA Output Source Current Capability
- High-Speed Serially Shifted Data Input
- Latches on All Driver Outputs

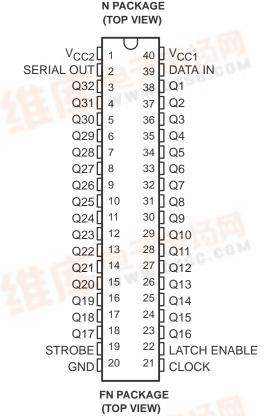
description

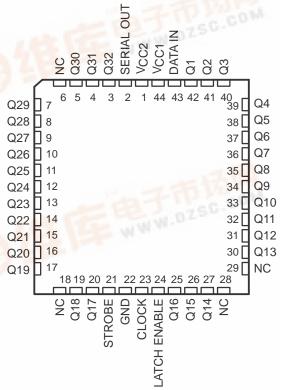
The SN65518 and SN75518 are monolithic BIDFET† integrated circuits designed to drive a dot matrix or segmented vacuum fluorescent display.

Each device consists of a 32-bit shift register, 32 latches, and 32 output AND gates. Serial data is entered into the shift register on the low-to-high transition of CLOCK. While LATCH ENABLE is high, parallel data is transferred to the output buffers through a 32-bit latch. Data present in the latch during the high-to-low transition of LATCH ENABLE is latched. When STROBE is low, all Q outputs are enabled. When STROBE is high, all Q outputs are low.

Serial data output from the shift register may be used to cascade additional devices. This output is not affected by LATCH ENABLE or STROBE.

The SN65518 is characterized for operation from -40° C to 85°C. The SN75518 is characterized for operation from 0°C to 70°C.



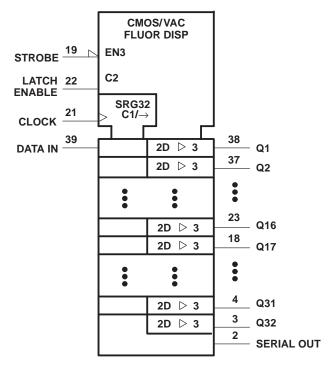


NC - No internal connection

BIDFET – Bipolar, double-diffused, N-channel and P-channel MOS transistors on same chip. This is a patented process.

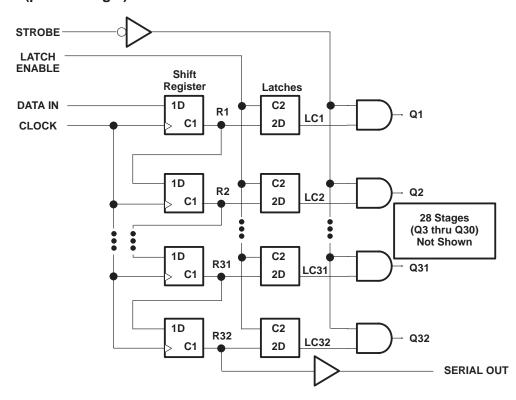


logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the N package.

logic diagram (positive logic)





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FUNCTION TABLE

FUNCTION	CONTROL INPUTS			SHIFT REGISTERS	LATCHES	OUTPUTS		
	CLOCK	LATCH ENABLE	STROBE	R1 THRU R32	LC1 THRU LC32	SERIAL	Q1 THRU Q32	
Load	↑ No ↑	X X	X X	Load and shift [†] No change	Determined by LATCH ENABLE‡	R32	Determined by STROBE	
Latch	X X	L H	X X	As determined above	Stored data New data	R32	Determined by STROBE	
Strobe	X X	X X	H L	As determined above	Determined by LATCH ENABLE‡	R32	All L LC1 thru LC32, respectively	

H = high level, L = low level, X = irrelevant, $\uparrow = low-to-high-level transition$.

typical operating sequence

CLOCK		
DATA IN	Valid	Irrelevant
SR Contents	Invalid	Valid
LATCH ENABLE		
Latch Contents	Previously Stored Data	New Data Valid
STROBE		
		
Q Outputs		Valid

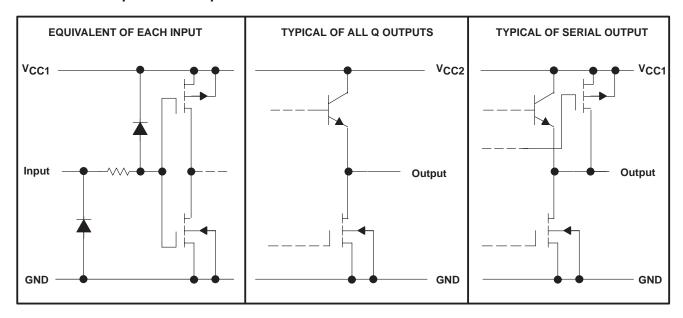


[†]R32 and the serial output take on the state of R31, R31 takes on the state of R30, ... R2 takes on the state of R1, and R1 takes on the state of the data input.

[‡] New data enter the latches while LATCH ENABLE is high. These data are stored while LATCH ENABLE is low.

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schematic of inputs and outputs



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V _{CC1} (see Note 1)	15 V
Supply voltage, V _{CC2}	70 V
Input voltage, V _I	V _{CC1}
Continuous total power dissipation See	Dissipation Rating Table
Operating free-air temperature range, T _A : SN65518	40°C to 85°C
SN75518	0°C to 70°C
Storage temperature range, T _{Stq}	65°C to 150°C
Case temperature for 10 seconds: FN package	260°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: N package	260°C

NOTE 1: Voltage values are with respect to network ground terminal.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING
FN	1700 mW	13.6 mW/°C	1088 mW	884 mW
N	1250 mW	10.0 mW/°C	800 mW	650 mW



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recommended operating conditions, $T_A = 25^{\circ}C$ (unless otherwise noted)

		MIN	MAX	UNIT
Supply voltage, V _{CC1}		4.5	15	V
Supply voltage, V _{CC2}		0	60	V
High-level input voltage, V _{IH} (see Figure 1)	V _{CC1} = 4.5 V	3.5		V
Tilgit-level iriput voltage, VIH (see Figure 1)	V _{CC1} = 15 V	12		V
Low-level input voltage, V _{IL} (see Figure 1)		-0.3	0.8	V
High-level output current, IOH			-25	mA
Low-level output current, IOL			2	mA
Clock frequency, f_{clock} (see Figure 2) $\frac{V_{CC1} = 10 \text{ V to } 15 \text{ V}}{V_{CC1} = 4.5 \text{ V}}$ Pulse duration, CLOCK high, $f_{cv}(CV)$	0	5	MHz	
Clock frequency, I _{Clock} (see Figure 2)	V _{CC1} = 4.5 V	0	1	IVITIZ
Pulso duration CLOCK high to cours	V _{CC1} = 10 V to 15 V	100		ns
ruise duration, CLOCK High, tw(CKH)	V _{CC1} = 4.5 V	500		115
Pulso duration CLOCK law to court	V _{CC1} = 10 V to 15 V	100		ns
ruise duration, CLOCK low, tw(CKL)	V _{CC1} = 4.5 V	500		115
Saturatima DATA IN hatara CLOCK↑ +	V _{CC1} = 10 V to 15 V	75		ns
Setup time, DATA IN Delote CLOCK I, tsu	V _{CC1} = 4.5 V	150		115
Hold time DATA IN ofter CLOCK® to	requency, f_{Clock} (see Figure 2)	75		no
Tiold time, DATA IN after CLOCKT, th	V _{CC1} = 4.5 V	150		ns
Operating free air temperature Te	SN65518	-40	85	°C
Operating free-air temperature, T _A	SN75518	0	70	

electrical characteristics over recommended ranges of operating free-air temperature and V_{CC1} , V_{CC2} = 60 V (unless otherwise noted)

PARAMETER			TEST CONDITIONS		MIN	TYP [†]	MAX	UNIT	
VIK	Input clamp voltage		I _I = -12 mA				-1.5	V	
1/2	Lligh lovel output voltage	Q outputs	$I_{OH} = -25 \text{ mA}$		57.5	58		V	
VOH	High-level output voltage	SERIAL OUT	$V_{CC1} = 5 V$,	I _{OH} = – 20 μA	4.5	4.9	5	V	
\/a.	Low lovel output voltoge	Q outputs	I _{OL} = 1 mA				5	٧	
VOL	Low-level output voltage	SERIAL OUT	I _{OL} = 20 μA			0.06	0.8		
lіН	High-level input current		V _{CC1} = 15 V,	V _I = 15 V	T	0.1	1	μΑ	
I _I L	Low-level input current		$V_{CC1} = 15 \text{ V},$	$V_I = 0 V$		-0.1	-1	μΑ	
loo.	Cupply ourront	h. ourroat	V _{CC1} = 4.5 V			1.8	4	mA	
ICC1	Supply current		V _{CC1} = 15 V			2	5	IIIA	
		SN65518	Outputs high,	$T_A = -40^{\circ}C$			12	mA	
ICC2	Supply current	SN65518,	Outputs high,	$T_A = 0$ °C to MAX		7	10		
		SN75518	Outputs low			0.01	0.5		

[†] All typical values are at $T_A = 25$ °C.

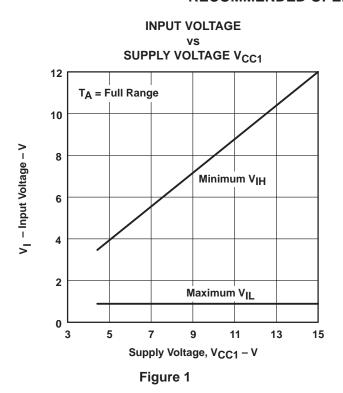


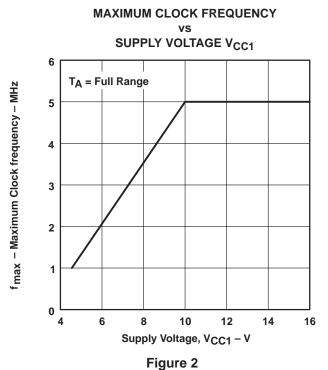
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switching characteristics, V_{CC2} = 60 V, C_L = 50 pF, T_A = 25°C (unless otherwise noted)

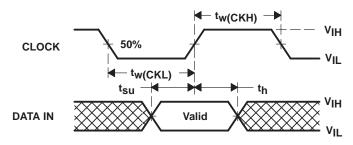
	PARAMETE	TEST CONDITIONS		MIN MAX	UNIT		
t _d Delay time, CLOCK to DATA OUT			V _{CC1} = 4.5 V	C _L = 15 pF,	600	ns	
^t d	Delay time, CLOCK to DATA OUT		V _{CC1} = 15 V	See Figure 4	150	119	
		From LATCH ENABLE	V _{CC1} = 4.5 V	See Figure 5	1.5	μs	
 	Delegations high to least level O output	From STROBE	VCC1 = 4.5 V	See Figure 6	1		
^t DHL	Delay time, high-to-low-level Q output	From LATCH ENABLE	V 15 V	See Figure 5	0.5		
		From STROBE	V _{CC1} = 15 V	See Figure 6	0.5		
		From LATCH ENABLE	V _{CC1} = 4.5 V	See Figure 5	1.5	μs	
 	Delay time, low-to-high-level Q output	From STROBE		See Figure 6	1		
tDLH		From LATCH ENABLE	V 45.V	See Figure 5	0.25		
		From STROBE	V _{CC1} = 15 V	See Figure 6	0.25		
t _{THL} Transition time, high-to-low-level Q output		4	V _{CC1} = 4.5 V		3		
		l	V _{CC1} = 15 V	See Figure 6	1.5	μs	
-	Transition time law to high lavel C output	4	V _{CC1} = 4.5 V	Soo Figuro 6	2.5		
^t TLH	Transition time, low-to-high-level Q output		V _{CC1} = 15 V	See Figure 6	0.75	μs	

RECOMMENDED OPERATING CONDITIONS





PARAMETER MEASUREMENT INFORMATION[†]



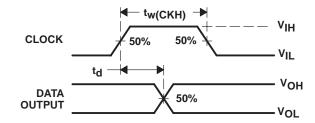
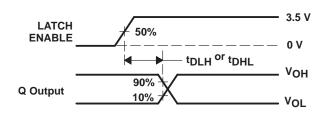


Figure 3. Input Timing Waveforms

Figure 4. Data Output Switching Times



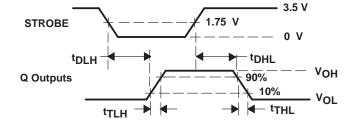


Figure 5. Q Output Switching Times

Figure 6. Switching Time Voltage Waveforms

 $[\]ensuremath{^{\dagger}}$ For testing purposes, all input pulses have maximum rise and fall times of 30 ns.

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